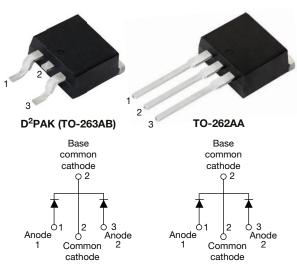
www.vishay.com

VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

Vishay Semiconductors

Ultrafast Rectifier, 2 x 10 A FRED Pt[®]



VS-MURB2020CT-M3

VS-MURB2020CT-1-M3

PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 10 A					
V _R	200 V					
V _F at I _F	0.85 V					
t _{rr}	35 ns					
T _J max.	175 °C					
Package	D ² PAK (TO-263AB), TO-262AA					
Circuit configuration	Common cathode					

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V _{RRM}		200	V
Average rectified forward current	per leg	I		10	
Average rectilied forward current	total device	I _{F(AV)}	Rated V _R , T _C = 145 °C	20	Α
Non-repetitive peak surge current per leg		I _{FSM}		100	~
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, $T_C = 145 \text{ °C}$	20	
Operating junction and storage tem	peratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	
		I _F = 8 A, T _J = 125 °C	-	-	0.85	V
Forward voltage	V _F	I _F = 16 A	-	-	1.15	
		I _F = 16 A, T _J = 125 °C	-	-	1.05	
Poverse leekage ourrept		$V_{\rm R} = V_{\rm R}$ rated	-	-	15	
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA
Junction capacitance	C _T	V _R = 200 V	-	55	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

Revision: 25-Oct-17

1

Document Number: 96391

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT

HALOGEN

FREE



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	A/μs, V _R = 30 V	-	-	35	
Reverse recovery time	+	I _F = 1.0 A, dI _F /dt = 100 A/μs, V _R = 30 V		-	19	-	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 10 A dI _F /dt = 200 A/μs V _R = 160 V	-	21	-	ns
		T _J = 125 °C		-	35	-	
Pools receivers ourrent	I _{RRM}	T _J = 25 °C		-	1.9	-	А
Peak recovery current		T _J = 125 °C		-	4.8	-	A
Poverse recovery charge	e recovery charge Q _{rr}	T _J = 25 °C		-	25	-	nC
Reverse recovery charge		T _J = 125 °C		-	78	-	no

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case per leg	R _{thJC}		-	-	2.5	
Thermal resistance, junction-to-ambient per leg	R _{thJA}		-	-	50	°C/W
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Case :	Case style D ² PAK (TO-263AB)	MURB2020CT				
Marking device		Case style TO-262AA		MURB2	020CT-1	

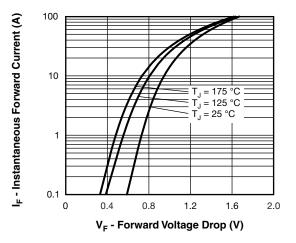


Fig. 1 - Typical Forward Voltage Drop Characteristics

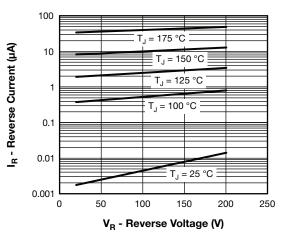


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

www.vishay.com

Vishay Semiconductors

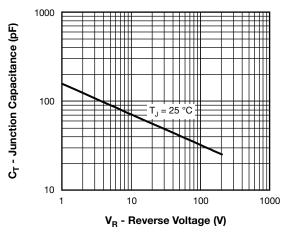


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

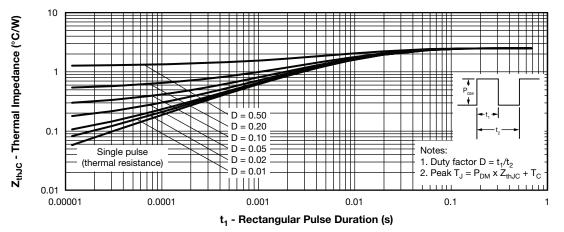
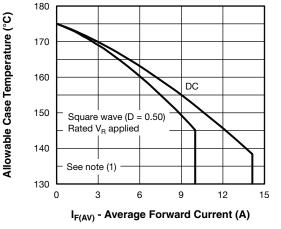
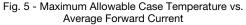


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





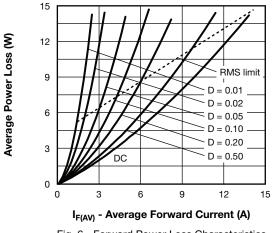


Fig. 6 - Forward Power Loss Characteristics

3

Document Number: 96391

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u> VISHAY. www.vishay.com

VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

Vishay Semiconductors

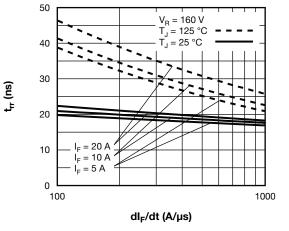
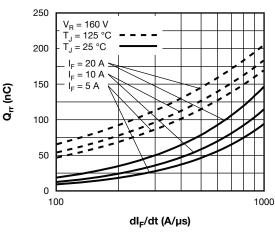
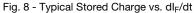


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

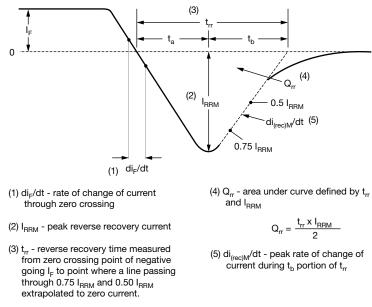


Fig. 9 - Reverse Recovery Waveform and Definitions

VISHAY, www.vishay.com

VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	MUR	В	20	20	ст	-1	L	-M3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)
		\bigcirc)))))	\bigcirc	\bigcirc
	1	- Visł	nay Sen	hicondu	ctors pro	oduct			
	2		_	JR serie					
	3	- B=	D ² PAK	(TO-26	3AB) / 1	0-2624	λA		
	4	- Cur	rent rati	ng (20 =	= 20 A)				
	5	- Volt	age rati	ng (20 =	= 200 V))			
	6	- ст	= cente	r tap (du	ial) TO-	220 / D ²	² PAK (⁻	FO-263/	AB) / T(
	7	- •-1	= TO-2	62AA					
		• No	one = D	² PAK (T	- O-263A	AB)			
	8	- • No	one = tu	be (50 p	pieces)				
				and reel	,	ented, fo	or D ² PA	к (то-:	263AB)
			•	and reel					,
	9		•	ntal digit		nonteu,		/ (10	/ 200AL
				gen-free		-complia	ant. and	l termin	ations le

	LINKS TO RELATED DOCUMENTS							
Dimensions —	D ² PAK (TO-263AB)	www.vishay.com/doc?96164						
	TO-262AA	www.vishay.com/doc?96165						
Part marking information —	D ² PAK (TO-263AB)	www.vishay.com/doc?95444						
	TO-262AA	www.vishay.com/doc?95443						
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424						
SPICE model		www.vishay.com/doc?95622						

Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	NOTES		
	STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25	BSC	0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

For technical questions within your region: DiodesAmericas@vishav.com, DiodesAsia@vishav.com, DiodesEurope@vishav.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



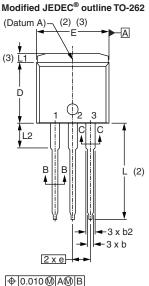
Outline Dimensions

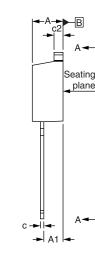


Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CVMPOI	MILLIN	IETERS	INC	HES	NOTEO
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	8.00 0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
 ⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis of the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Rectifiers category:

Click to view products by Vishay manufacturer:

Other Similar products are found below :

 70HFR40
 RL252-TP
 150KR30A
 1N5397
 NTE5841
 NTE6038
 SCF5000
 1N4002G
 1N4005-TR
 JANS1N6640US
 481235F

 RRE02VS6SGTR
 067907F
 MS306
 70HF40
 T110HF60
 T85HFL60S02
 US2JFL-TP
 A1N5404G-G
 CRS04(T5L,TEMQ)
 ACGRA4007-HF

 ACGRB207-HF
 CLH03(TE16L,Q)
 ACGRC307-HF
 ACEFC304-HF
 NTE6356
 NTE6359
 NTE6002
 NTE6023
 NTE6039
 NTE6077

 85HFR60
 40HFR60
 1N1186RA
 70HF120
 85HFR80
 D126A45C
 SCF7500
 D251N08B
 SCHJ22.5K
 SM100
 SCPA2
 SCH10000
 SDHD5K

 VS-12FL100S10
 ACGRA4001-HF
 D1821SH45T PR
 D1251S45T
 NTE5990
 NTE6358